Maximum Ratings / Höchstzulässige Werte

Parameter	Condition		Symbol	Values	Unit
				max.	
Input Rectifier Bridge **Gleichrichter**					
Repetitive peak reverse voltage Periodische Rückw. Spitzensperrspannung			V_{RRM}	1600	V
Forward current per diode Dauergrenzstrom	DC current	T_h=80°C; Tc=80°C	I_{FAV}	58 80	A
Surge forward current Stoßstrom Grenzwert	t_p=10ms	T_j=25°C	I_{FSM}	700	A
I^2t-value Grenzlastintegral	t_p=10ms	T_j=25°C	I^2t	2450	A^2s
Power dissipation per Diode Verlustleistung pro Diode	T_j=150°C	T_h=80°C T_c=80°C	P_{tot}	62 93	W
max. chip temperature max. Chiptemperatur			T_{jmax}	150	°C
Transistor Inverter **Transistor Wechselrichter**					
Collector-emitter break down voltage Kollektor-Emitter-Sperrspannung			V_{CE}	600	V
DC collector current Kollektor-Dauergleichstrom	T_j=T_{jmax}	T_h=80°C T_c=80°C	I_C	65 85	A
Repetitive peak collector current Periodischer Kollektorspitzenstrom	t_p limted by T_{jmax}		I_{cpuls}	225	A
Power dissipation per IGBT Verlustleistung pro IGBT	T_j=T_{jmax}	T_h=80°C T_c=80°C	P_{tot}	105 160	W
Gate-emitter peak voltage Gate-Emitter-Spitzenspannung			V_{GE}	±20	V
SC withstand time * Kurzschlußverhalten *	Tj≤150°C V_{CC}=360V	V_{GE}=15V	t_{SC}	5	us
max. chip temperature max. Chiptemperatur			T_{jmax}	175	°C
Diode Inverter **Diode Wechselrichter**					
DC forward current Dauergleichstrom	T_j=T_{jmax}	T_h=80°C, T_c=80°C	I_F	52 55, limted by bond wires	A
Repetitive peak forward current Periodischer Spitzenstrom	t_p limted by T_{jmax}		I_{FRM}	225	A
Power dissipation per Diode Verlustleistung pro Diode	T_j=150°C	T_h=80°C T_c=80°C	P_{tot}	77 120	W
max. chip temperature max. Chiptemperatur			T_{jmax}	175	°C

Maximum Ratings / Höchstzulässige Werte

Parameter	Condition	Symbol	Values	Unit
			max.	
Transistor BRC **Transistor BRC**				
Collector-emitter break down voltage Kollektor-Emitter-Sperrspannung		V_{CE}	600	V
DC collector current Kollektor-Dauergleichstrom	$T_j=T_{jmax}$ $T_h=80°C$ $T_c=80°C$	I_C	65 85	A
Repetitive peak collector current Periodischer Kollektorspitzenstrom	t_p limted by T_{jmax}	I_{cpuls}	225	A
Power dissipation per IGBT Verlustleistung pro IGBT	$T_j=T_{jmax}$ $T_h=80°C$ $T_c=80°C$	P_{tot}	105 160	W
Gate-emitter peak voltage Gate-Emitter-Spitzenspannung		V_{GE}	±20	V
SC withstand time * Kurzschlußverhalten *	Tj≤150°C V_{GE}=15V V_{CC}=360V	t_{SC}	5	us
max. chip temperature max. Chiptemperatur		T_{jmax}	175	°C
Diode BRC **Diode BRC**				
DC forward current Dauergleichstrom	$T_j=T_{jmax}$ $T_h=80°C$, $T_c=80°C$	I_F	52 55, limted by bond wires	A
Repetitive peak forward current Periodischer Spitzenstrom	t_p limted by T_{jmax}	I_{FRM}	225	A
Power dissipation per Diode Verlustleistung pro Diode	$T_j=150°C$ $T_h=80°C$ $T_c=80°C$	P_{tot}	77 120	W
max. chip temperature max. Chiptemperatur		T_{jmax}	175	°C
Thermal properties **Thermische Eigenschaften**				
Storage temperature Lagertemperatur		T_{stg}	-40…+125	°C
Operation temperature Betriebstemperatur		T_{op}	-40…+125	°C
Insulation properties **Modulisolation**				
Insulation voltage Isolationsspannung	t=1min	V_{is}	4000	Vdc
Creepage distance Kriechstrecke			min 12,7	mm
Clearance Luftstrecke			min 12,7	mm

* Allowed number of short circuits must be less than 1000 times, and time duration between short circuits should be more than 1 second!

Characteristic values

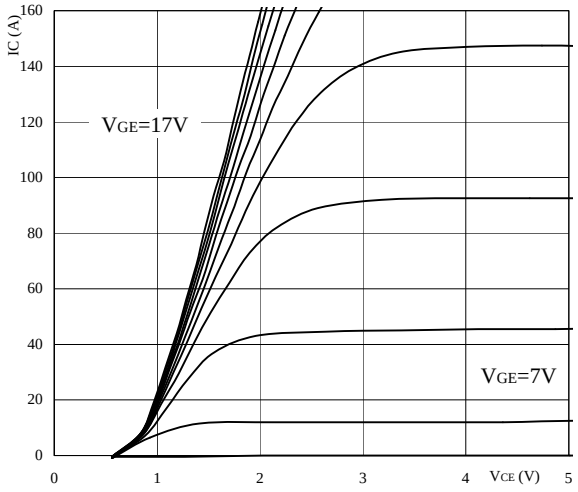
Description	Symbol	Conditions					Values			Unit
		T(C°)	Other conditions (Rgon-Rgoff)	V_{GE}(V) V_{GS}(V)	V_R(V) V_{CE}(V) V_{DS}(V)	Ic(A) IF(A) Id(A)	Min	Typ	Max	
Input Rectifier Bridge **Gleichrichter**										
Forward voltage Durchlaßpannung	V_F	Tj=25°C Tj=125°C				35	0,8	1,02 0,94	1,35	V
Threshold voltage (for power loss calc. only) Schleusenspannung	V_{to}	Tj=25°C Tj=125°C				 35		0,88 0,75		V
Slope resistance (for power loss calc. only) Ersatzwiderstand	r_t	Tj=25°C Tj=125°C				 35		0,004 0,006		Ohm
Reverse current Sperrstrom	I_r	Tj=25°C Tj=140±10°C			1500 1500		0 0		0,1 2	mA
Thermal resistance chip to heatsink per chip Wärmewiderstand Chip-Kühlkörper pro Chip	R_{thJH}		Thermal grease thickness≤50um					1,14		K/W
Thermal resistance chip to case per chip Wärmewiderstand Chip-Gehause pro Chip	R_{thJC}		Warmeleitpaste Dicke≤50um λ = 0,61 W/mK					0,75		K/W
Transistor Inverter **Transistor Wechselrichter**										
Gate emitter threshold voltage Gate-Schwellenspannung	$V_{GE(th)}$	Tj=25°C Tj=125°C	VCE=VGE			0,0015	4	5,8	8	V
Collector-emitter saturation voltage Kollektor-Emitter Sättigungsspannung	$V_{CE(sat)}$	Tj=25°C Tj=125°C				75	1,3	1,5 1,65	2,15	V
Collector-emitter cut-off current incl. Diode Kollektor-Emitter Reststrom	I_{CES}	Tj=25°C Tj=125°C		0	600				0,5	mA
Gate-emitter leakage current Gate-Emitter Reststrom	I_{GES}	Tj=25°C Tj=125°C		20	0				700	nA
Integrated Gate resistor Integrirter Gate Widerstand	R_{gint}							4		Ohm
Turn-on delay time Einschaltverzögerungszeit	$t_{d(on)}$	Tj=25°C Tj=125°C	Rgoff= 4 Ohm Rgon= 4 Ohm	 ±15	 300	 75		 130		ns
Rise time Anstiegszeit	t_r	Tj=25°C Tj=125°C	Rgoff= 4 Ohm Rgon= 4 Ohm	 ±15	 300	 75		 28		ns
Turn-off delay time Abschaltverzögerungszeit	$t_{d(off)}$	Tj=25°C Tj=125°C	Rgoff= 4 Ohm Rgon= 4 Ohm	 ±15	 300	 75		 275		ns
Fall time Fallzeit	t_f	Tj=25°C Tj=125°C	Rgoff= 4 Ohm Rgon= 4 Ohm	 ±15	 300	 75		 65		ns
Turn-on energy loss per pulse Einschaltverlustenergie pro Puls	E_{on}	Tj=25°C Tj=125°C	Rgoff= 4 Ohm Rgon= 4 Ohm	 ±15	 300	 75		 1,3		mWs
Turn-off energy loss per pulse Abschaltverlustenergie pro Puls	E_{off}	Tj=25°C Tj=125°C	Rgoff= 4 Ohm Rgon= 4 Ohm	 ±15	 300	 75		 2,1		mWs
Input capacitance Eingangskapazität	C_{ies}	Tj=25°C Tj=125°C	f=1MHz	0	25			4,75		nF
Output capacitance Ausgangskapazität	C_{oss}	Tj=25°C Tj=125°C	f=1MHz	0	25			0,3		nF
Reverse transfer capacitance Rückwirkungskapazität	C_{rss}	Tj=25°C Tj=125°C	f=1MHz	0	25			0,15		nF
Gate charge Gate Ladung	Q_{Gate}	Tj=25°C Tj=125°C	Rgoff= 4 Ohm Rgon= 4 Ohm	 ±15	 300	 75		 730		nC
Thermal resistance chip to heatsink per chip Wärmewiderstand Chip-Kühlkörper pro Chip	R_{thJH}		Thermal grease thickness≤50um					0,9		K/W
Thermal resistance chip to case per chip Wärmewiderstand Chip-Gehause pro Chip	R_{thJC}		Warmeleitpaste Dicke≤50um λ = 0,61 W/mK					0,6		K/W
Diode Inverter **Diode Wechselrichter**										
Diode forward voltage Durchlaßspannung	V_F	Tj=25°C Tj=125°C				75	1	1,85 1,8	2,6	V
Peak reverse recovery current Rückstromspitze	I_{RM}	Tj=25°C Tj=125°C	Rgon= 4 Ohm diF/dt = 3300 A/us	 -15	 300	 75		 88		A
Reverse recovery time Sperreverzögerungszeit	t_{rr}	Tj=25°C Tj=125°C	Rgon= 4 Ohm diF/dt = 3300 A/us	 -15	 300	 75		 165		ns
Reverse recovered charge Sperrverzögerungsladung	Q_{rr}	Tj=25°C Tj=125°C	Rgon= 4 Ohm diF/dt = 3300 A/us	 -15	 300	 75		 5,5		uC
Reverse recovered energy Sperrverzögerungsenergie	Erec	Tj=25°C Tj=125°C	Rgon= 4 Ohm diF/dt = 3300 A/us	 -15	 300	 75		 1,25		mWs
Thermal resistance chip to heatsink per chip Wärmewiderstand Chip-Kühlkörper pro Chip	R_{thJH}		Thermal grease thickness≤50um					1,25		K/W
Thermal resistance chip to case per chip Wärmewiderstand Chip-Gehause pro Chip	R_{thJC}		Warmeleitpaste Dicke≤50um λ = 0,61 W/mK					0,8		K/W

Characteristic values

Description	Symbol	Conditions					Values			Unit
		T(C°)	Other conditions (Rgon-Rgoff)	V_{GE}(V) V_{GS}(V)	V_R(V) V_{CE}(V) V_{DS}(V)	Ic(A) IF(A) Id(A)	Min	Typ	Max	
Transistor BRC										
Transistor BRC										
Gate emitter threshold voltage	$V_{GE(th)}$	Tj=25°C	VCE=VGE			0,0015	4	5,8	8	V
Gate-Schwellenspannung		Tj=125°C								
Collector-emitter saturation voltage	$V_{CE(sat)}$	Tj=25°C				75	1,3	1,5	2,15	V
Kollektor-Emitter Sättigungsspannung		Tj=125°C						1,65		
Collector-emitter cut-off	I_{CES}	Tj=25°C		0	600				0,5	mA
Kollektor-Emitter Reststrom		Tj=125°C								
Gate-emitter leakage current	I_{GES}	Tj=25°C		20	0				700	nA
Gate-Emitter Reststrom		Tj=125°C								
Integrated Gate resistor	R_{gint}							4		Ohm
Integrirter Gate Widerstand										
Turn-on delay time	$t_{d(on)}$	Tj=25°C	Rgoff= 4 Ohm							ns
Einschaltverzögerungszeit		Tj=125°C	Rgon= 4 Ohm	±15	300	75		130		
Rise time	t_r	Tj=25°C	Rgoff= 4 Ohm							ns
Anstiegszeit		Tj=125°C	Rgon= 4 Ohm	±15	300	75		28		
Turn-off delay time	$t_{d(off)}$	Tj=25°C	Rgoff= 4 Ohm							ns
Abschaltverzögerungszeit		Tj=125°C	Rgon= 4 Ohm	±15	300	75		275		
Fall time	t_f	Tj=25°C	Rgoff= 4 Ohm							ns
Fallzeit		Tj=125°C	Rgon= 4 Ohm	±15	300	75		65		
Turn-on energy loss per pulse	E_{on}	Tj=25°C	Rgoff= 4 Ohm							mWs
Einschaltverlustenergie pro Puls		Tj=125°C	Rgon= 4 Ohm	±15	300	75		1,3		
Turn-off energy loss per pulse	E_{off}	Tj=25°C	Rgoff= 4 Ohm							mWs
Abschaltverlustenergie pro Puls		Tj=125°C	Rgon= 4 Ohm	±15	300	75		2,1		
Input capacitance	C_{iss}	Tj=25°C	f=1MHz	0	25			4,75		nF
Eingangskapazität		Tj=125°C								
Output capacitance	C_{oss}	Tj=25°C	f=1MHz	0	25			0,3		nF
Ausgangskapazität		Tj=125°C								
Reverse transfer capacitance	C_{ies}	Tj=25°C	f=1MHz	0	25			0,15		nF
Rückwirkungskapazität		Tj=125°C								
Gate charge	Q_{gate}	Tj=25°C	Rgoff= 4 Ohm							nC
Gate Ladung		Tj=125°C	Rgon= 4 Ohm	±15	300	75		730		
Thermal resistance chip to heatsink per chip			Thermal grease							
Wärmewiderstand Chip-Kühlkörper pro Chip	R_{thJH}		thickness≤50um					0,9		K/W
Thermal resistance chip to case per chip			Warmeleitpaste Dicke≤50um							
Wärmewiderstand Chip-Gehause pro Chip	R_{thJC}		λ = 0,61 W/mK					0,6		K/W
Diode BRC										
Diode BRC										
Diode forward voltage	V_F	Tj=25°C				75	1	1,85	2,6	V
Durchlaßspannung		Tj=125°C						1,8		
Reverse current	I_r	Tj=25°C	Rgon= 4 Ohm							A
Sperrstrom		Tj=125°C	diF/dt = 3300 A/us	-15	300	75		88		
Reverse recovery time	t_{rr}	Tj=25°C	Rgon= 4 Ohm							ns
Sperreverzögerungszeit		Tj=125°C	diF/dt = 3300 A/us	-15	300	75		165		
Reverse recovered charge	Q_{rr}	Tj=25°C	Rgon= 4 Ohm							uC
Sperrverzögerungsladung		Tj=125°C	diF/dt = 3300 A/us	-15	300	75		5,5		
Reverse recovery energy	E_{rec}	Tj=25°C	Rgon= 4 Ohm							mWs
Sperrverzögerungsenergie		Tj=125°C	diF/dt = 3300 A/us	-15	300	75		1,25		
Thermal resistance chip to heatsink per chip			Thermal grease							
Wärmewiderstand Chip-Kühlkörper pro Chip	R_{thJH}		thickness≤50um					1,25		K/W
Thermal resistance chip to case per chip			Warmeleitpaste Dicke≤50um							
Wärmewiderstand Chip-Gehause pro Chip	R_{thJC}		λ = 0,61 W/mK					0,8		K/W
PTC-Thermistor										
PTC-Widerstand										
Nominal resistance	R_{25}	Tj=25°C	tolerance = 3%				0,97	1	1,03	kOhm
Nominaler Widerstand	R_{100}	Tj=100°C	tolerance = 2%				1,637	1,67	1,703	kOhm
Typical temperature coefficient	α	Tj=25°C						0,76		%/K
Tipischer Temperaturkoeffizient		Tj=125°C								
Recommended measuring current		Tj=25°C					1		3	
Empfohlener Messstrom	I_m	Tj=125°C								mA
Measured values		Tj=25°C	I_m = 1mA				0,93		1,03	
Gemessene Werte	V_{PTC}		I_m = 3mA				2,84		3,4	V

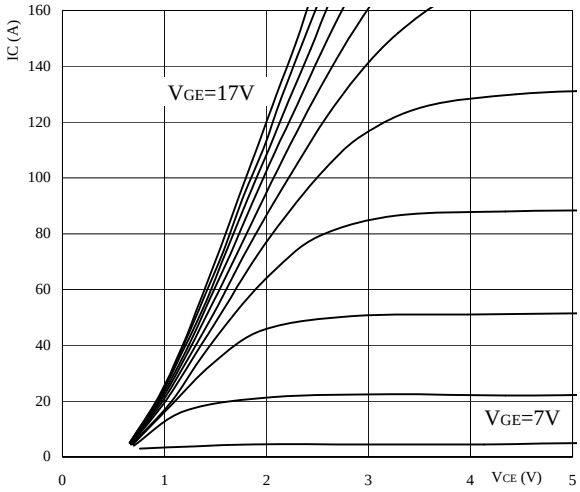
Output inverter

Figure 1. **Typical output characteristics**
Output inverter IGBT
Ic= f(VCE)



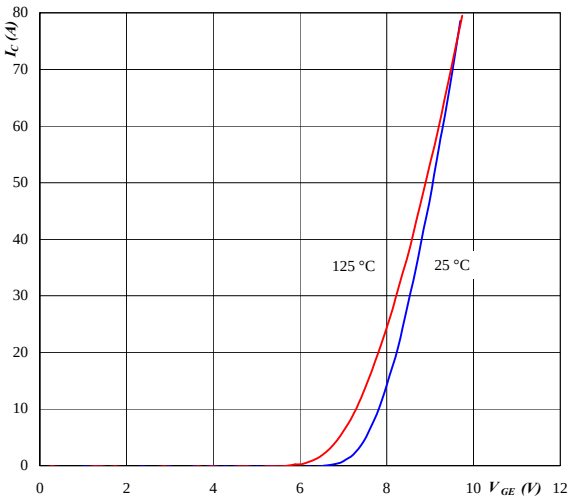
parameter: tp = 250 us Tj = 25 °C
VGE parameter: from: 7 V to 17 V
in 1 V steps

Figure 2. **Typical output characteristics**
Output inverter IGBT
Ic= f(VCE)



parameter: tp = 250 us Tj = 125 °C
VGE parameter: from: 7 V to 17 V
in 1 V steps

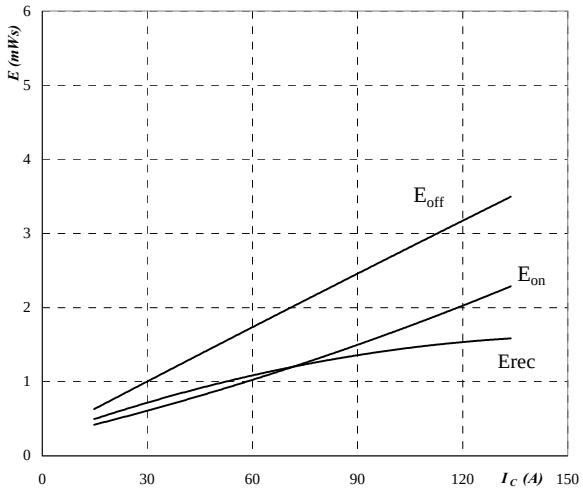
Figure 3. **Typical transfer characteristics**
Output inverter IGBT
Ic= f(VGE)



parameter: tp = 250 us VCE = 10 V

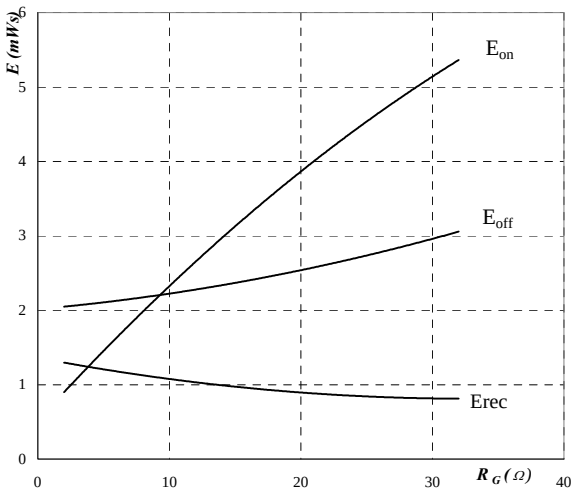
Output inverter

Figure 4. **Typical switching energy losses as a function of collector current**
Output inverter IGBT
E = f (Ic)



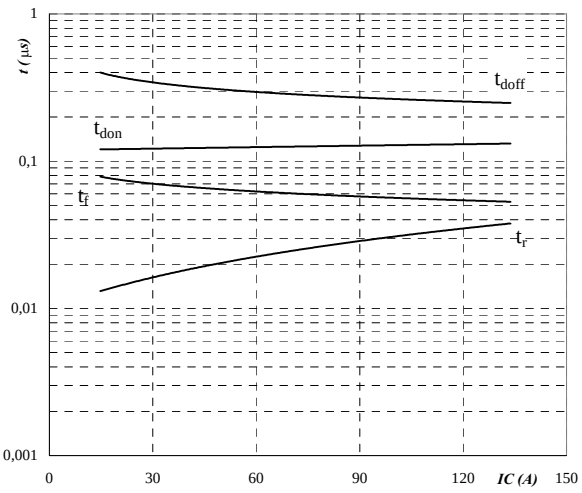
inductive load, Tj = 125 °C
VCE = 300 V
VGE= ±15 V
Rgon= 4 Ω
Rgoff= 4 Ω

Figure 5. **Typical switching energy losses as a function of gate resistor**
Output inverter IGBT
E = f (RG)



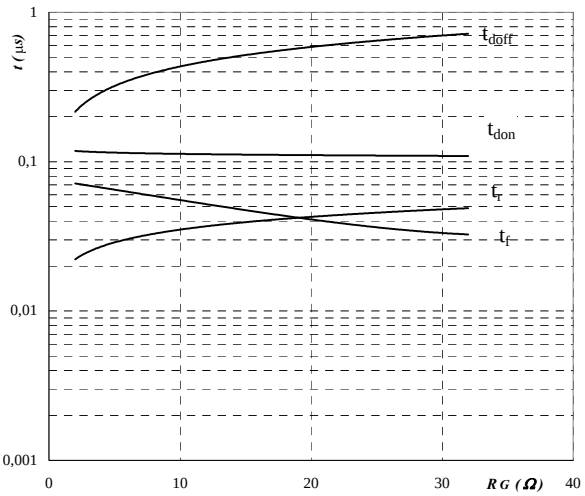
inductive load, Tj = 125 °C
VCE = 300 V
VGE= ±15 V
Ic = 75 A

Figure 6. **Typical switching times as a function of collector current**
Output inverter IGBT
t = f (Ic)



inductive load, Tj = 125 °C
VCE = 300 V
VGE= ±15 V
Rgon= 4 Ω
Rgoff= 4 Ω

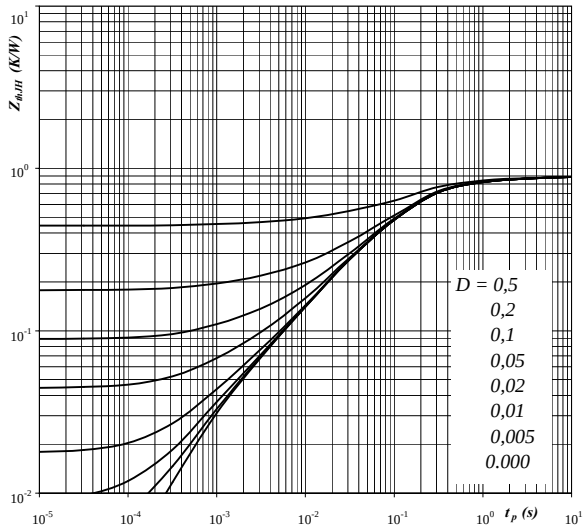
Figure 7. **Typical switching times as a function of gate resistor**
Output inverter IGBT
t = f (RG)



inductive load, Tj = 125 °C
VCE = 300 V
VGE= ±15 V
Ic = 75 A

Output inverter

Figure 8. IGBT transient thermal impedance as a function of pulse width
$Z_{thJH} = f(tp)$



Parameter: D = tp / T RthJH= 0,90 K/W

IGBT thermal model values

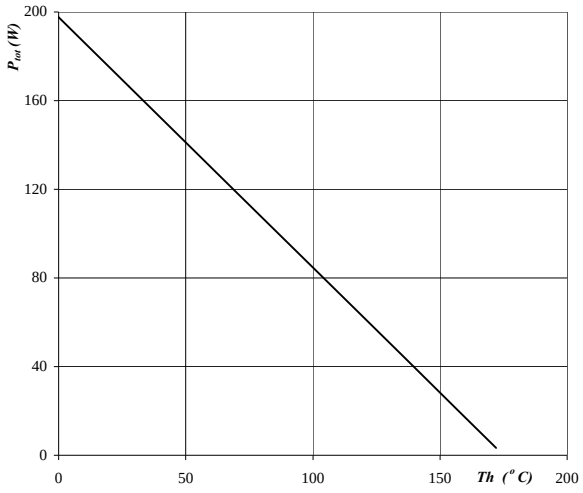
R (C/W)	Tau (s)
0,06	3,3E+00
0,18	4,9E-01
0,50	1,1E-01
0,12	1,3E-02
0,03	1,1E-03

Output inverter

Figure 9. Power dissipation as a function of heatsink temperature

Output inverter IGBT

P_{tot} = f (Th)

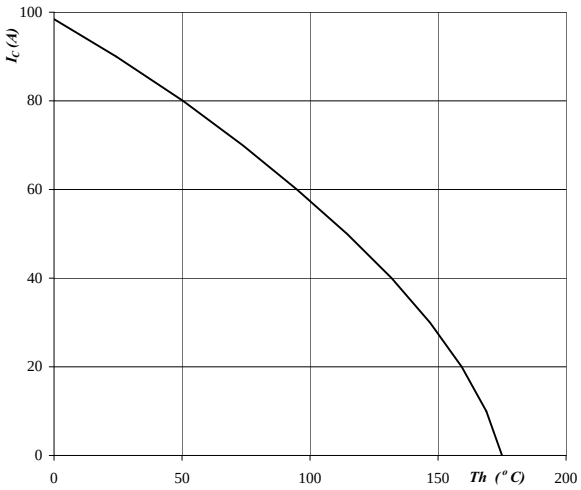


parameter: Tj = 175°C

Figure 10. Collector current as a function of heatsink temperature

Output inverter IGBT

I_C = f (Th)



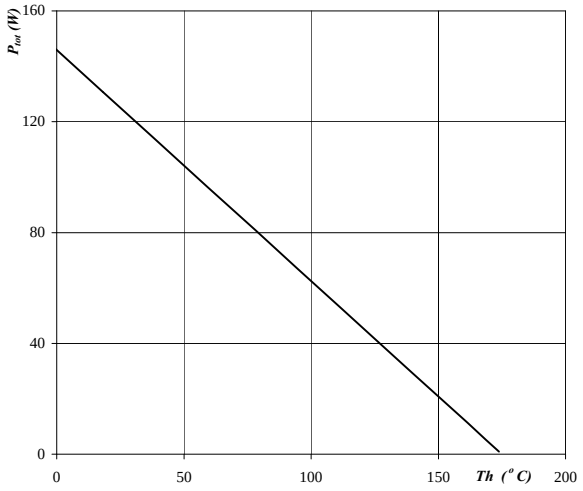
parameter: Tj = 175°C

V_{GE}= 15 V

Figure 11. Power dissipation as a function of heatsink temperature

Output inverter FRED

P_{tot} = f (Th)

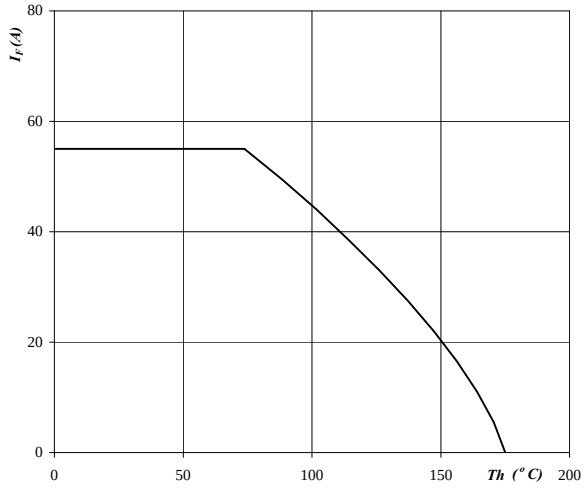


parameter: Tj = 175°C

Figure 12. Forward current as a function of heatsink temperature

Output inverter FRED

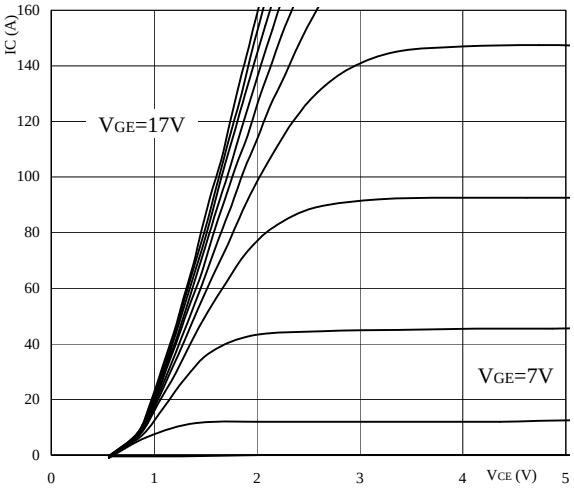
I_F = f (Th)



parameter: Tj = 175°C

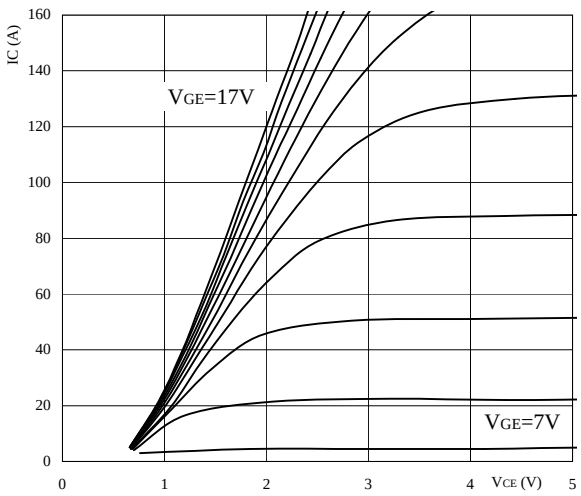
Brake

Figure 13. Typical output characteristics
Brake IGBT
Ic= f(VCE)



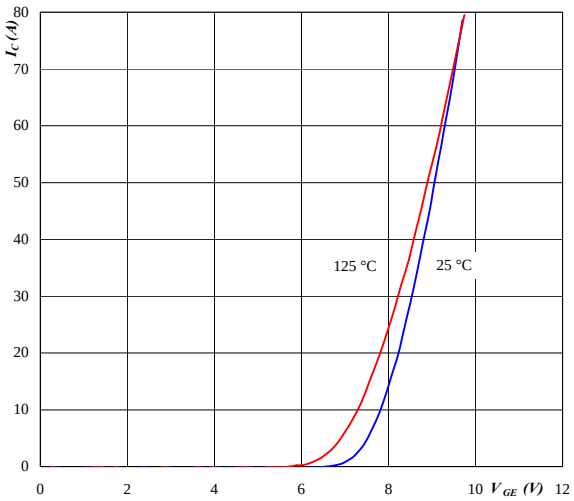
parameter: tp = 250 us Tj = 25 °C
VGE parameter: from: 7 V to 17 V
in 1 V steps

Figure 14. Typical output characteristics
Brake IGBT
Ic= f(VCE)



parameter: tp = 250 us Tj = 125 °C
VGE parameter: from: 7 V to 17 V
in 1 V steps

Figure 15. Typical transfer characteristics
Brake IGBT
Ic= f(VGE)



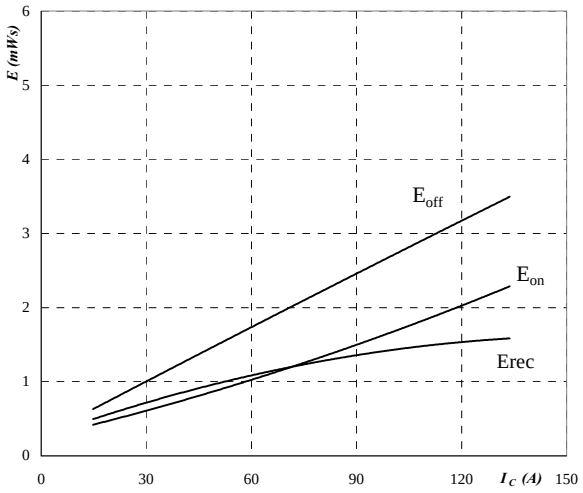
parameter: tp = 250 us VCE = 10 V

Brake

Figure 16. Typical switching energy losses as a function of collector current

Brake IGBT

E = f (Ic)



inductive load, Tj = 125 °C

V_{CE} = 300 V

V_{GE} = ±15 V

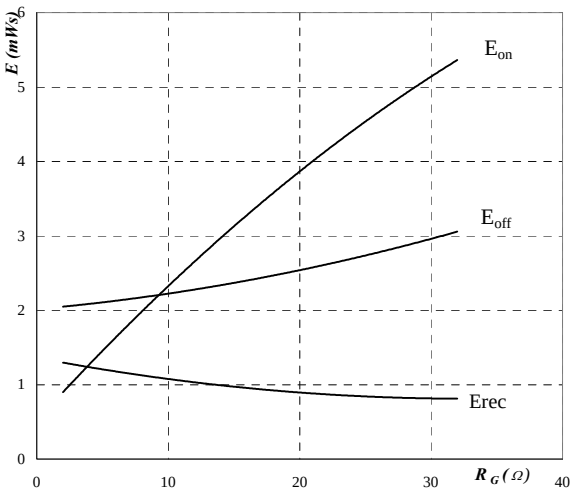
Rgon = 4 Ω

Rgoff = 4 Ω

Figure 17. Typical switching energy losses as a function of gate resistor

Brake IGBT

E = f (R_G)



inductive load, Tj = 125 °C

V_{CE} = 300 V

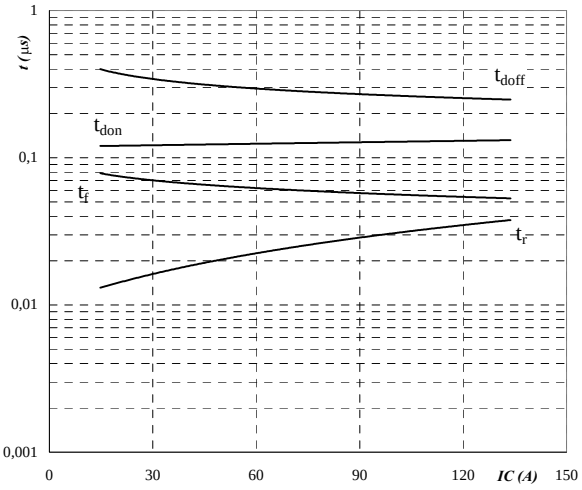
V_{GE} = ±15 V

Ic = 75 A

Figure 18. Typical switching times as a function of collector current

Brake IGBT

t = f (Ic)



inductive load, Tj = 125 °C

V_{CE} = 300 V

V_{GE} = ±15 V

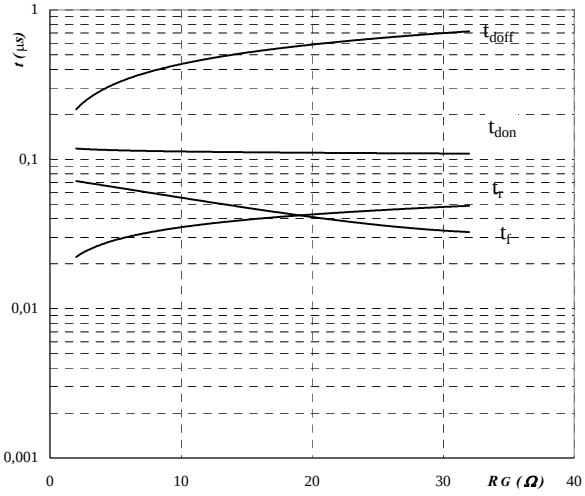
Rgon = 4 Ω

Rgoff = 4 Ω

Figure 19. Typical switching times as a function of gate resistor

Brake IGBT

t = f (R_G)



inductive load, Tj = 125 °C

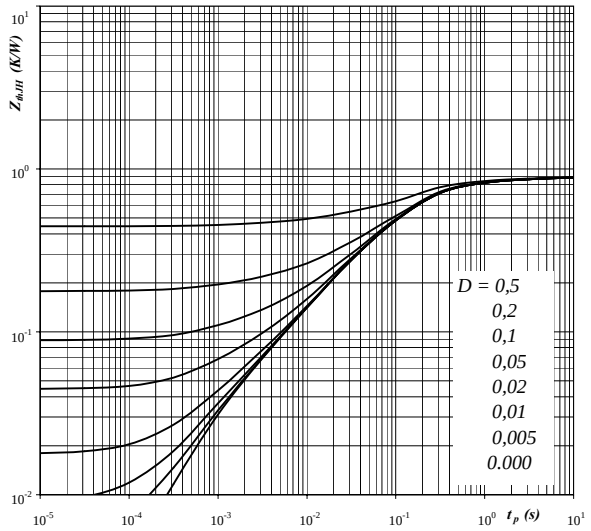
V_{CE} = 300 V

V_{GE} = ±15 V

Ic = 75 A

Brake

Figure 20. IGBT transient thermal impedance as a function of pulse width
$Z_{thJH} = f(tp)$

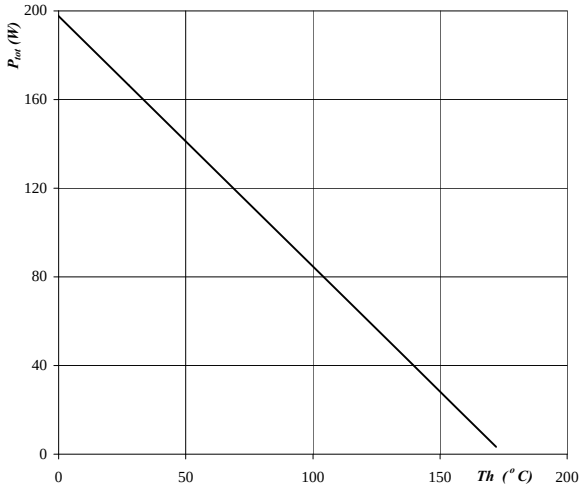


Parameter: D = tp / T RthJH= 0,90 K/W

IGBT thermal model values

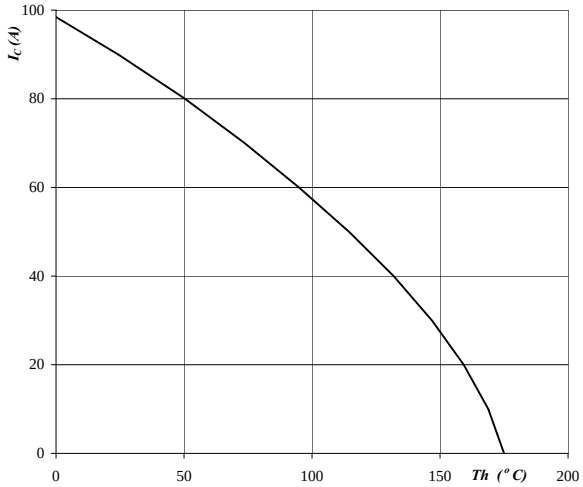
R (C/W)	Tau (s)
0,06	3,3E+00
0,18	4,9E-01
0,50	1,1E-01
0,12	1,3E-02
0,03	1,1E-03

Figure 21. Power dissipation as a function of heatsink temperature
Brake IGBT
$P_{tot} = f(Th)$



parameter: Tj = 175°C

Figure 22. Collector current as a function of heatsink temperature
Brake IGBT
$I_C = f(Th)$

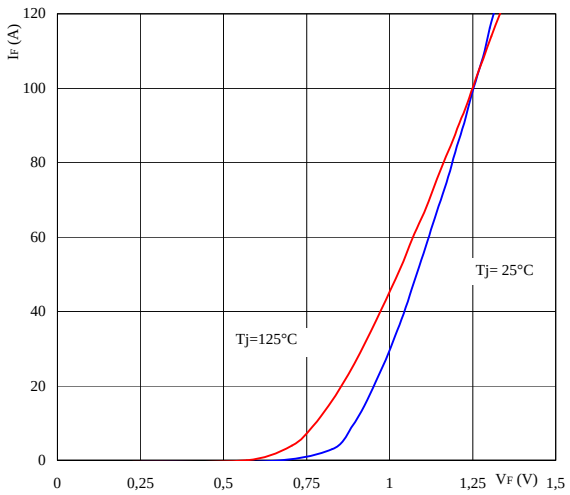


parameter: Tj = 175°C
V_{GE}= 15 V

Input rectifier bridge

Figure 23. Typical diode forward current as a function of forward voltage

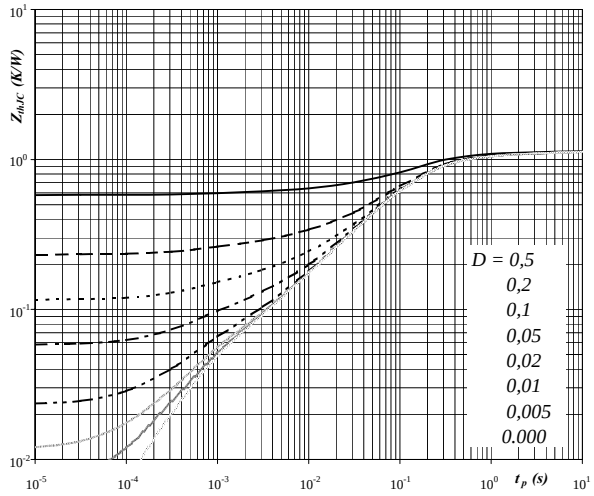
Rectifier diode $I_F=f(V_F)$



parameter: tp = 250 us

Figure 24. Diode transient thermal impedance as a function of pulse width

$Z_{thJH} = f(tp)$

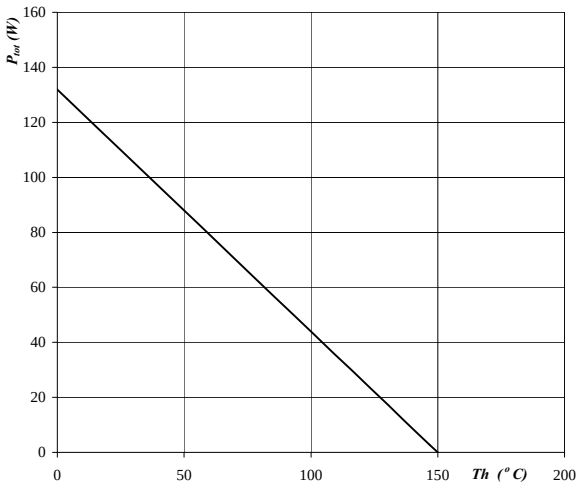


Parameter: D = tp / T RthJH= 1,14 K/W

Figure 25. Power dissipation as a function of heatsink temperature

Rectifier diode

$P_{tot} = f (Th)$

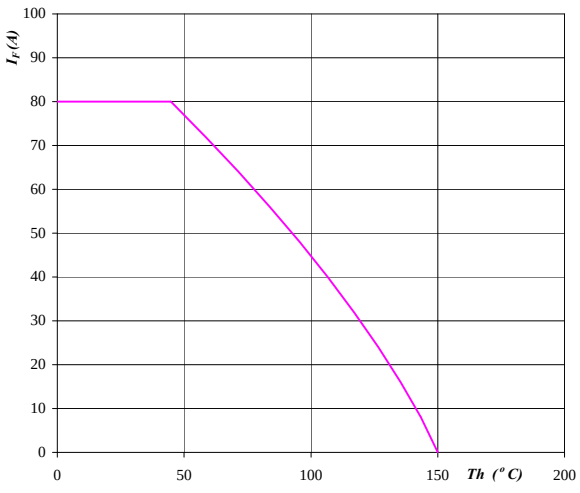


parameter: Tj = 150°C

Figure 26. Forward current as a function of heatsink temperature

Rectifier diode

$I_F = f (Th)$



parameter: Tj = 150°C

Thermistor

Figure 27. Typical PTC characteristic as afunction of temperature

$R_T = f(T)$